LISTING OF CLAIMS

1. (Original) A semiconductor polishing composition comprising:

fumed silica, the semiconductor polishing composition being an aqueous dispersion solution of fumed silica,

wherein a content of the fumed silica having a particle diameter of 100 nm or less is 15% by volume or more based on a total amount of the fumed silica.

2. (Original) The semiconductor polishing composition of claim 1, wherein a content of fumed silica having a particle diameter of 100 nm or less is in a range of 15 to 90% by volume based on a total amount of the fumed silica.

3. (Previously Presented) The semiconductor polishing composition of claim 1, wherein, in a particle size distribution by volume of the fumed silica, the semiconductor polishing composition has a particle size of the maximum frequency in a range of 115 nm or less.

4. (Previously Presented) The semiconductor polishing composition of claim 1, wherein, in a particle size distribution by volume of the fumed silica, the semiconductor polishing composition has a particle size of the maximum frequency in a range of 80 to 115 nm.

5. (Previously Presented) The semiconductor polishing composition of claim 1, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

6. (Previously Presented) The semiconductor polishing composition of claim 1, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

7. (Original) The semiconductor polishing composition of claim 6, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.

8. (Previously Presented) The semiconductor polishing composition of claim 2, wherein, in a particle size distribution by volume of the fumed silica, the semiconductor polishing composition has a particle size of the maximum frequency in a range of 115 nm or less.

9. (Previously Presented) The semiconductor polishing composition of claim 2, wherein, in a particle size distribution by volume of the fumed silica, the semiconductor polishing composition has a particle size of the maximum frequency in a range of 80 to 115 nm.

10. (Previously Presented) The semiconductor polishing composition of claim 3, wherein, in a particle size distribution by volume of the fumed silica, the semiconductor polishing composition has a particle size of the maximum frequency in a range of 80 to 115 nm.

11. (Previously Presented) The semiconductor polishing composition of claim 8, wherein, in a particle size distribution by volume of the fumed silica, the semiconductor polishing composition has a particle size of the maximum frequency in a range of 80 to 115 nm.

12. (Previously Presented) The semiconductor polishing composition of claim 2, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

13. (Previously Presented) The semiconductor polishing composition of claim 3, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

14. (Previously Presented) The semiconductor polishing composition of claim 4, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

15. (Previously Presented) The semiconductor polishing composition of claim 2, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

16. (Previously Presented) The semiconductor polishing composition of claim 3, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

17. (Previously Presented) The semiconductor polishing composition of claim 4, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

18. (Previously Presented) The semiconductor polishing composition of claim 5, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.